

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type ( $\pi$ -MOSVI)

## 2SK3567

### Switching Regulator Applications

- Low drain-source ON resistance:  $R_{DS(ON)} = 1.7\ \Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 2.5S$  (typ.)
- Low leakage current:  $I_{DSS} = 100\ \mu A$  ( $V_{DS} = 600\ V$ )
- Enhancement mode:  $V_{th} = 2.0\sim 4.0\ V$  ( $V_{DS} = 10\ V, I_D = 1\ mA$ )

### Absolute Maximum Ratings ( $T_a = 25^\circ C$ )

| Characteristics                                |                                | Symbol    | Rating   | Unit       |
|--|--------------------------------|-----------|----------|------------|
| Drain-source voltage                           |                                | $V_{DSS}$ | 600      | V          |
| Drain-gate voltage ( $R_{GS} = 20\ k\Omega$ )  |                                | $V_{DGR}$ | 600      | V          |
| Gate-source voltage                            |                                | $V_{GSS}$ | $\pm 30$ | V          |
| Drain current                                  | DC (Note 1)                    | $I_D$     | 3.5      | A          |
|  | Pulse ( $t = 1\ ms$ ) (Note 1) | $I_{DP}$  | 14       |            |
| Drain power dissipation ( $T_c = 25^\circ C$ ) |                                | $P_D$     | 35       | W          |
| Single pulse avalanche energy (Note 2)         |                                | $E_{AS}$  | 201      | mJ         |
| Avalanche current                              |                                | $I_{AR}$  | 3.5      | A          |
| Repetitive avalanche energy (Note 3)           |                                | $E_{AR}$  | 3.5      | mJ         |
| Channel temperature                            |                                | $T_{ch}$  | 150      | $^\circ C$ |
| Storage temperature range                      |                                | $T_{stg}$ | -55~150  | $^\circ C$ |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

### Thermal Characteristics

| Characteristics                        | Symbol         | Max  | Unit         |
|--|----------------|------|--------------|
| Thermal resistance, channel to case    | $R_{th(ch-c)}$ | 3.57 | $^\circ C/W$ |
| Thermal resistance, channel to ambient | $R_{th(ch-a)}$ | 62.5 | $^\circ C/W$ |

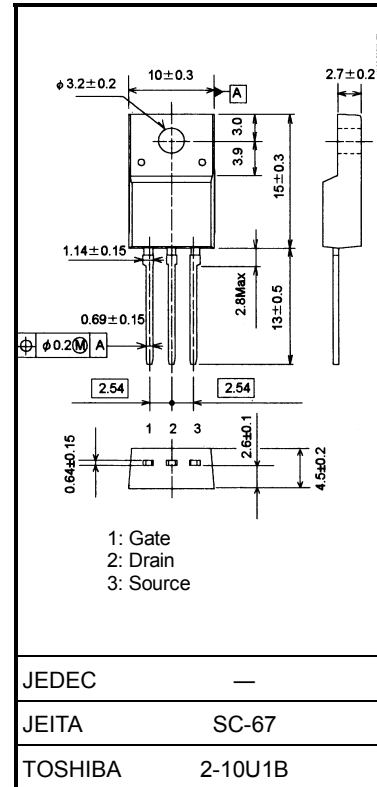
Note 1: Ensure that the channel temperature does not exceed  $150^\circ C$ .

Note 2:  $V_{DD} = 90\ V, T_{ch} = 25^\circ C$ (initial),  $L = 28.8\ mH, I_{AR} = 3.5\ A, R_G = 25\ \Omega$

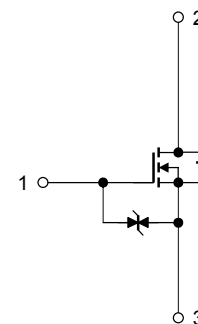
Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Please handle with caution.

Unit: mm



Weight : 1.7 g (typ.)



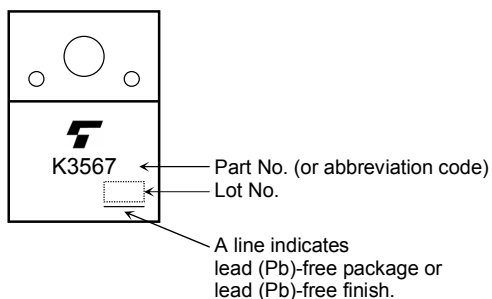
## Electrical Characteristics (Ta = 25°C)

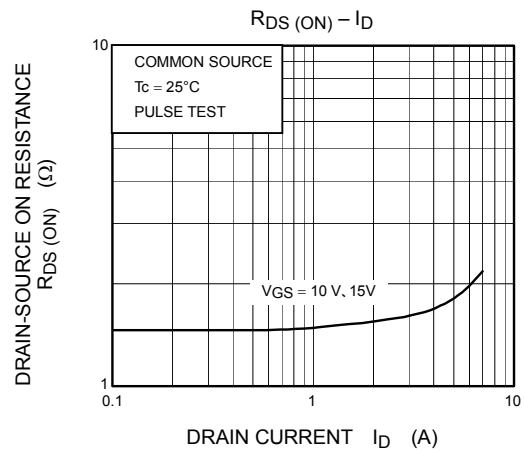
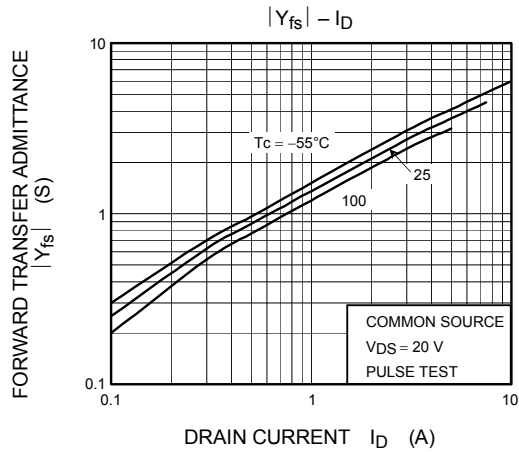
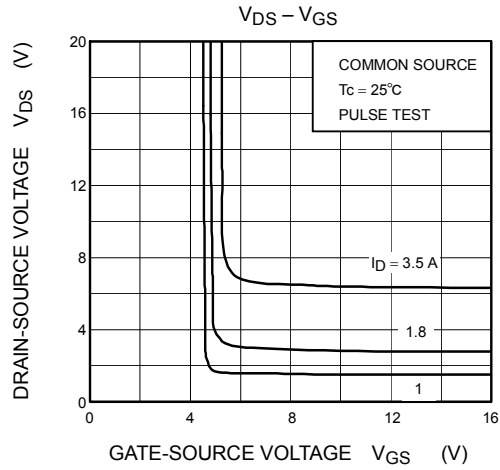
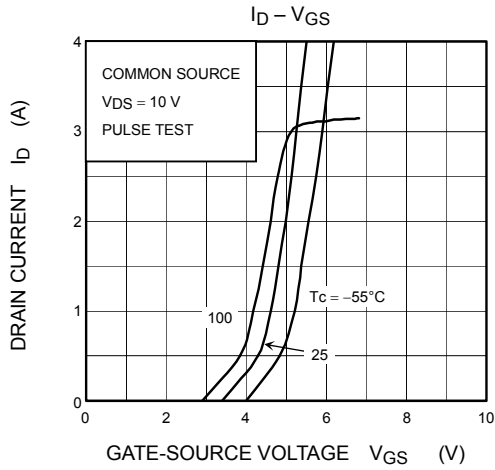
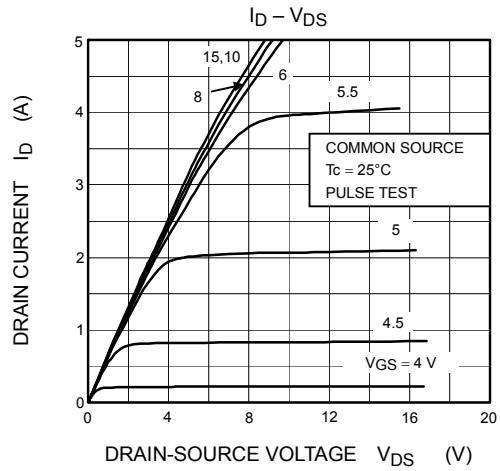
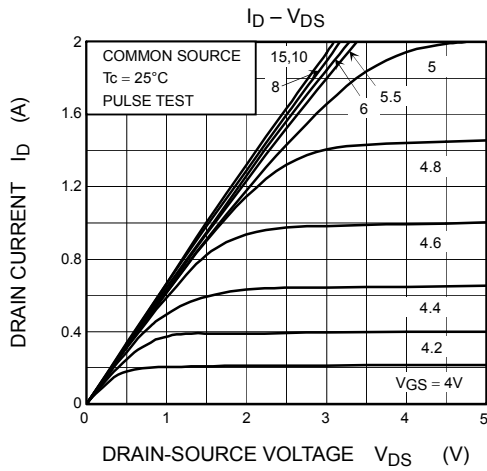
| Characteristics                |               | Symbol        | Test Condition   | Min                                      | Typ. | Max      | Unit          |
|--------------------------------|---------------|---------------|--|--|------|----------|---------------|
| Gate leakage current           |               | $I_{GSS}$     | $V_{GS} = \pm 25 \text{ V}, V_{DS} = 0 \text{ V}$                          | —  | —    | $\pm 10$ | $\mu\text{A}$ |
| Gate-source breakdown voltage  |               | $V_{(BR)GSS}$ | $I_G = \pm 10 \mu\text{A}, V_{DS} = 0 \text{ V}$                           | $\pm 30$                                 | —    | —        | V             |
| Drain cut-off current          |               | $I_{DSS}$     | $V_{DS} = 600 \text{ V}, V_{GS} = 0 \text{ V}$                             | —  | —    | 100      | $\mu\text{A}$ |
| Drain-source breakdown voltage |               | $V_{(BR)DSS}$ | $I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$                                | 600                                      | —    | —        | V             |
| Gate threshold voltage         |               | $V_{th}$      | $V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$                                | 2.0                                      | —    | 4.0      | V             |
| Drain-source ON resistance     |               | $R_{DS(ON)}$  | $V_{GS} = 10 \text{ V}, I_D = 1.8 \text{ A}$                               | —  | 1.7  | 2.2      | $\Omega$      |
| Forward transfer admittance    |               | $ Y_{fs} $    | $V_{DS} = 10 \text{ V}, I_D = 1.8 \text{ A}$                               | 0.7                                      | 2.5  | —        | S             |
| Input capacitance              |               | $C_{iss}$     | $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$           | —  | 550  | —        | pF            |
| Reverse transfer capacitance   |               | $C_{rss}$     |  | —  | 6    | —        |               |
| Output capacitance             |               | $C_{oss}$     |  | —  | 60   | —        |               |
| Switching time                 | Rise time     | $t_r$         |  | —  | 12   | —        | ns            |
|                                | Turn-on time  | $t_{on}$      |  | —  | 45   | —        |               |
|                                | Fall time     | $t_f$         |  | —  | 13   | —        |               |
|                                | Turn-off time | $t_{off}$     |  | Duty $\leq 1\%$ , $t_w = 10 \mu\text{s}$ | —    | 80       |               |
| Total gate charge              |               | $Q_g$         | $V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 3.5 \text{ A}$ | —  | 16   | —        | nC            |
| Gate-source charge             |               | $Q_{gs}$      |  | —  | 10   | —        |               |
| Gate-drain charge              |               | $Q_{gd}$      |  | —  | 6    | —        |               |

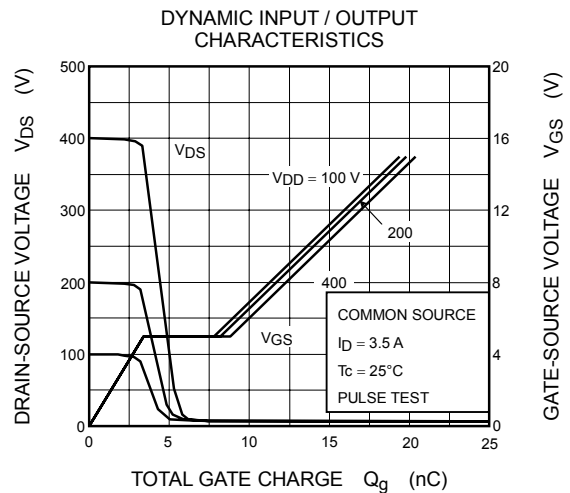
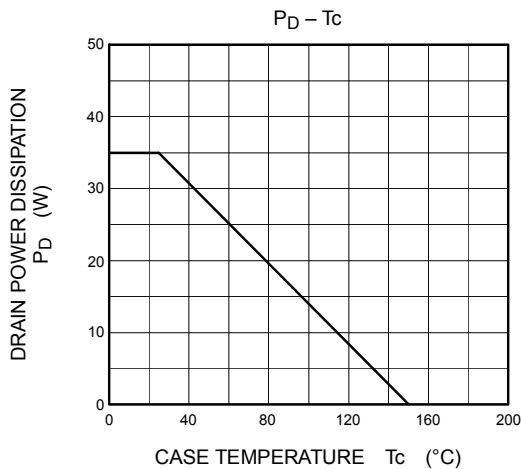
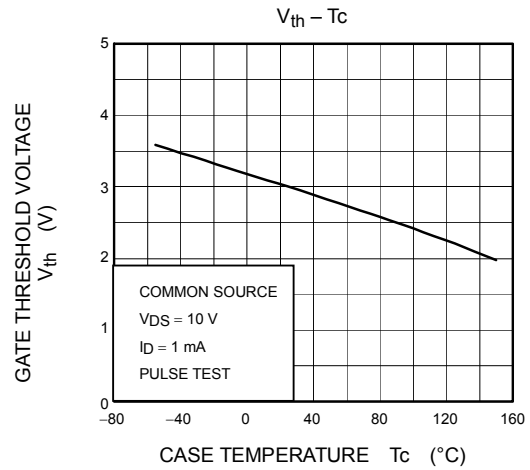
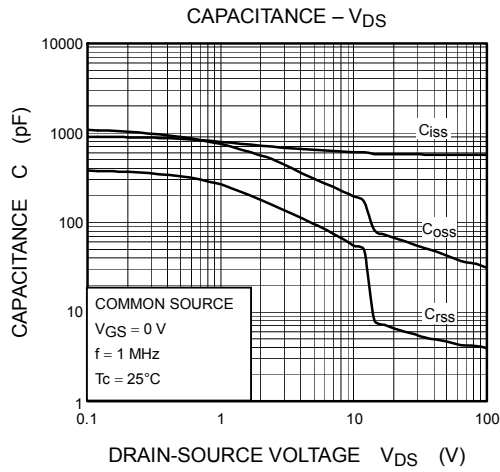
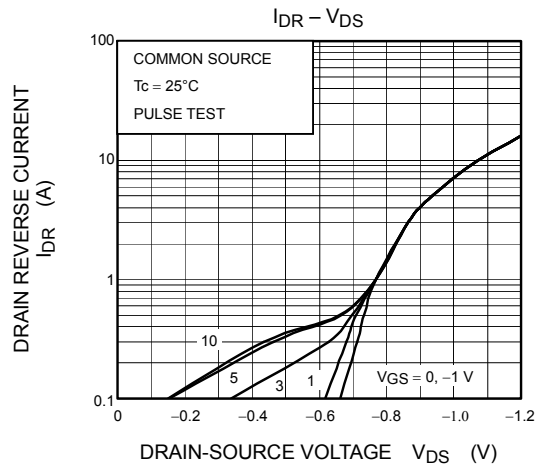
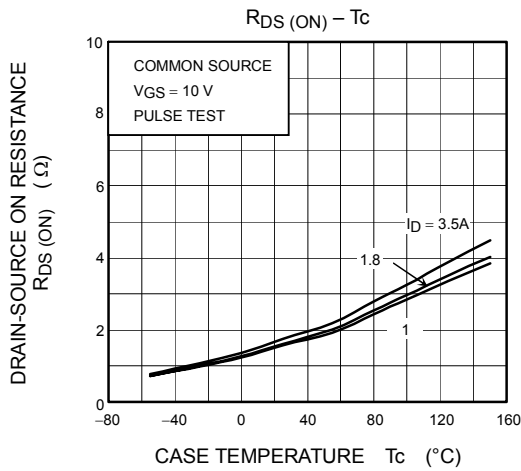
## Source-Drain Ratings and Characteristics (Ta = 25°C)

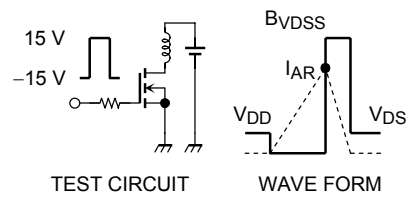
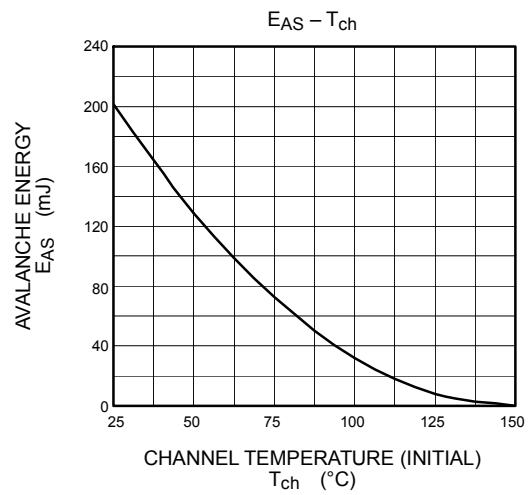
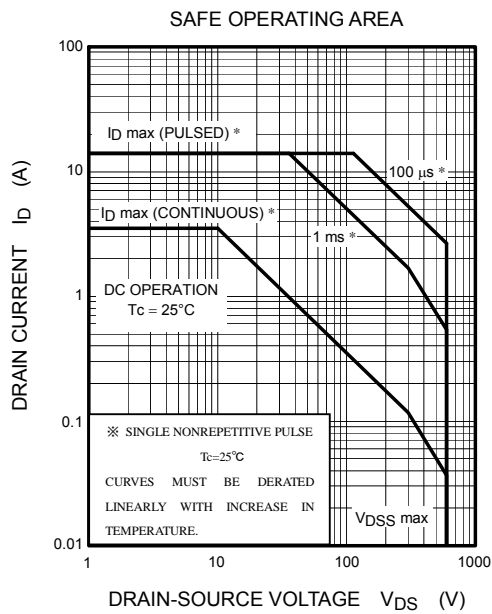
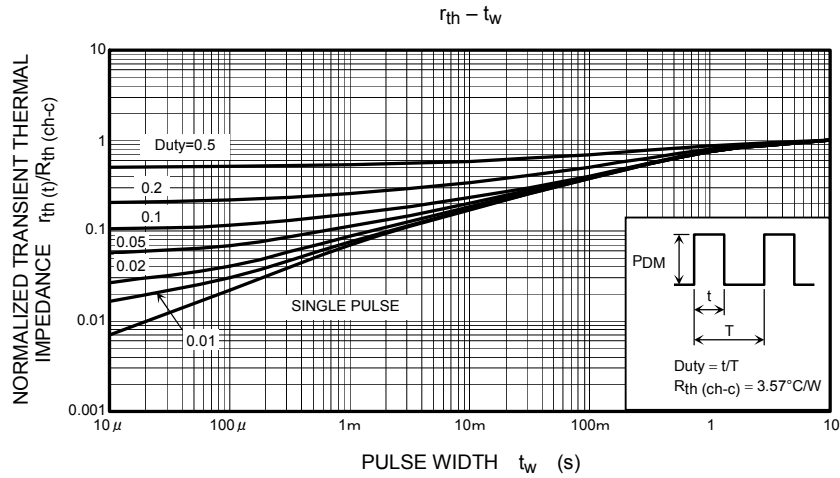
| Characteristics                              |  | Symbol    | Test Condition  | Min | Typ. | Max  | Unit          |
|--|--|-----------|---|-----|------|------|---------------|
| Continuous drain reverse current<br>(Note 1) |  | $I_{DR}$  | —   | —   | —    | 3.5  | A             |
| Pulse drain reverse current<br>(Note 1)      |  | $I_{DRP}$ | —   | —   | —    | 14   | A             |
| Forward voltage (diode)                      |  | $V_{DSF}$ | $I_{DR} = 3.5 \text{ A}, V_{GS} = 0 \text{ V}$  | —   | —    | -1.7 | V             |
| Reverse recovery time                        |  | $t_{rr}$  | $I_{DR} = 3.5 \text{ A}, V_{GS} = 0 \text{ V},$<br>$dI_{DR}/dt = 100 \text{ A}/\mu\text{s}$ | —   | 1400 | —    | ns            |
| Reverse recovery charge                      |  | $Q_{rr}$  |   | —   | 9.0  | —    | $\mu\text{C}$ |

## Marking









$R_G = 25 \Omega$

$V_{DD} = 90 V, L = 28.8 mH$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left( \frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$

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